

**CLAIM AMENDMENTS**

Please amend the claims as described below. In accordance with 37 CFR §1.121, a complete listing of all claims in the application is provided below. Notably, the status of each claim is indicated in the parenthetical expression adjacent to the corresponding claim number.

**Claims 1-31 (Canceled).**

1       **32. (Previously Presented)** An electromechanical device comprising:  
2       a substrate  
3       an insulation layer disposed on the substrate,  
4       a first semiconductor layer disposed on the insulation layer;  
5       an anchor that is disposed in an opening in the insulation layer and the first  
6       semiconductor layer and contacts the substrate, wherein the anchor includes a material  
7       that is different than the insulation layer;  
8       a second semiconductor layer, disposed on the anchor; and  
9       a fixed electrode, formed in part from the second semiconductor layer, wherein the  
10      fixed electrode is affixed to the substrate via the anchor.

1       **33. (Previously Presented)** The device of claim 32 wherein the anchor includes  
2      silicon nitride, silicon carbide, germanium, silicon/germanium or gallium arsenide.

1       **34. (Previously Presented)** The device of claim 32 wherein the insulation layer  
2      includes silicon nitride or silicon oxide.

1           35. **(Previously Presented)** The device of claim 32 further including a moveable  
2 electrode, juxtaposed the fixed electrode, wherein the moveable electrode is formed in part  
3 from the second semiconductor layer.

1           36. **(Currently Amended)** The device of claim 35 wherein the insulation layer is  
2 ~~comprised of~~ includes silicon oxide and the anchor material includes silicon nitride, silicon  
3 carbide, germanium, silicon/germanium or gallium arsenide.

1           37. **(Currently Amended)** The device of claim 35 wherein the insulation layer is  
2 ~~comprised of~~ includes silicon oxide and the anchor material includes silicon, silicon carbide,  
3 germanium, silicon/germanium, or gallium arsenide.

1           38. **(Currently Amended)** The device of claim 35 wherein the insulation layer is  
2 ~~comprised of~~ includes silicon nitride and the anchor material includes silicon, silicon oxide,  
3 silicon carbide, germanium, silicon/germanium or gallium arsenide.

1           39. **(Previously Presented)** The device of claim 32 wherein a substantial portion  
2 of the fixed electrode overlying the anchor material is a monocrystalline silicon.

1           40. **(Previously Presented)** The device of claim 32 wherein a substantial portion  
2 of the fixed electrode overlying the anchor material is a polycrystalline silicon.

1           41. **(Currently Amended)** The device of claim 32 further including:

2 a chamber, defined in part by including a first encapsulation layer having at least  
3 one vent;  
4 a moveable electrode disposed in the chamber and juxtaposed the fixed electrode;  
5 a second encapsulation layer ~~comprised of a semiconductor material~~, deposited  
6 over or in the vent, to thereby seal the chamber, wherein the second encapsulation layer  
7 includes a semiconductor material.

1 42. (Currently Amended) The device of claim 41 wherein the second  
2 encapsulation layer ~~is comprised of~~ includes polycrystalline silicon, porous polycrystalline  
3 silicon, amorphous silicon, silicon carbide, silicon/germanium, germanium or gallium  
4 arsenide.

1 43. (Currently Amended) The device of claim 42 wherein the first encapsulation  
2 layer ~~is comprised of~~ includes polycrystalline silicon, porous polycrystalline silicon,  
3 amorphous silicon, germanium, silicon/germanium, gallium arsenide, silicon nitride or  
4 silicon carbide.

1 44. (Previously Presented) The device of claim 41 wherein:  
2 the first encapsulation layer is a semiconductor material that is doped with a first  
3 impurity to provide a first region of a first conductivity type, and  
4 the semiconductor material of the second encapsulation layer is doped with a  
5 second impurity to provide a second region with a second conductivity type and wherein  
6 the first conductivity type is opposite the second conductivity type.

1           **45. (Currently Amended)** The device of claim 41 further including a contact having  
2   at least a portion that is disposed outside the chamber.

1           **46. (Currently Amended)** The device of claim 41 wherein a first portion of the first  
2   encapsulation layer is ~~comprised of~~ a monocrystalline silicon and a second portion of the  
3   first encapsulation layer is ~~comprised of~~ a polycrystalline silicon.

1           **47. (Currently Amended)** The device of claim 41 wherein a first portion of the first  
2   encapsulation layer is ~~comprised of~~ a monocrystalline silicon and a second portion of the  
3   first encapsulation layer is ~~comprised of~~ a porous or amorphous silicon.

1           **48. (Previously Presented)** The device of claim 47 wherein the second  
2   encapsulation layer overlying the second portion of the first encapsulation layer is a  
3   polycrystalline silicon.

1           **49. (Currently Amended)** The device of claim 48 includes a field region disposed  
2   outside and above the chamber wherein the field region is ~~comprised of~~ a monocrystalline  
3   silicon.

1           **50. (Currently Amended)** An electromechanical device comprising:  
2   a substrate  
3   an insulation layer disposed on the substrate,  
4   a first semiconductor layer disposed on the insulation layer;

5 an anchor that is disposed in an opening in the insulation layer and the first  
6 semiconductor layer and contacts the substrate, wherein the anchor includes a material  
7 that is different than the insulation layer;  
8 a second semiconductor layer, disposed on the anchor; and  
9 a fixed electrode, formed in part from the second semiconductor layer, wherein the  
10 fixed electrode is affixed to the substrate via the anchor;  
11 a moveable electrode, formed in part from the second semiconductor layer, wherein  
12 the moveable electrode is disposed in a chamber wherein the chamber ~~includes~~ is defined  
13 in part by a first encapsulation layer;  
14 a second encapsulation layer ~~comprised of a semiconductor material~~, deposited  
15 over or in the vent, to thereby seal the chamber, wherein the second encapsulation layer  
16 includes a semiconductor material;  
17 a contact; and  
18 a trench, disposed around at least a portion of the contact, wherein ~~the contact and~~  
19 the trench ~~as~~ is disposed outside the chamber and wherein the trench includes a first  
20 material disposed therein to electrically isolate the contact.

1 51. (Currently Amended) The device of claim 50 wherein the second  
2 encapsulation layer ~~is comprised of~~ includes polycrystalline silicon, porous polycrystalline  
3 silicon, amorphous silicon, silicon carbide, silicon/germanium, germanium, or gallium  
4 arsenide.

1           **52. (Currently Amended)** The device of claim 51 wherein the first encapsulation  
2 layer ~~is comprised of~~ includes polycrystalline silicon, porous polycrystalline silicon,  
3 amorphous silicon, germanium, silicon/germanium, gallium arsenide, silicon nitride or  
4 silicon carbide.

1           **53. (Currently Amended)** The device of claim 50 wherein the first material ~~is an~~  
2 ~~insulating material~~ is disposed on at least the outer surfaces of the trench.

1           **54. (Previously Presented)** The device of claim 53 wherein the trench includes a  
2 second material surrounded by the first material and wherein the second material is a  
3 semiconductor material.

1           **55. (Previously Presented)** The device of claim 53 wherein the trench is disposed  
2 on an etch stop region.

1           **56. (Previously Presented)** The device of claim 53 wherein the etch stop region is  
2 a silicon nitride or silicon dioxide.

1           **57. (Previously Presented)** The device of claim 53 wherein the first material is a  
2 silicon nitride or silicon dioxide.

1           **58. (Previously Presented)** The device of claim 53 wherein the trench surrounds  
2 the contact.

1           **59. (Previously Presented)** The device of claim 50 wherein the anchor includes  
2   silicon nitride, silicon carbide, germanium, silicon/germanium or gallium arsenide.

1           **60. (Previously Presented)** The device of claim 50 wherein the insulation layer  
2   includes silicon nitride or silicon oxide.

1           **61. (Currently Amended)** The device of claim 50 wherein the insulation layer  
2   includes ~~is comprised of~~ silicon oxide and the anchor material includes silicon nitride,  
3   silicon carbide, germanium, silicon/germanium or gallium arsenide.

1           **62. (Currently Amended)** The device of claim 50 wherein the insulation layer  
2   includes ~~is comprised of~~ silicon nitride and the anchor material includes silicon, silicon  
3   oxide, silicon carbide, germanium, silicon/germanium or gallium arsenide.

1           **63. (Previously Presented)** The device of claim 50 wherein a substantial portion  
2   of the fixed electrode overlying the anchor material is a monocrystalline silicon.

1           **64. (Previously Presented)** The device of claim 50 wherein a substantial portion  
2   of the fixed electrode overlying the anchor material is a polycrystalline silicon.